



Dual N-Channel 60-V (D-S) MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A)	Q _g (Typ.)		
60	0.060 at V _{GS} = 10 V	4.8	13		
	0.075 at V _{GS} = 4.5 V	4.3	13		

FEATURES

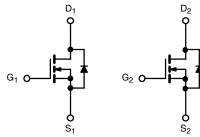
- Halogen-free According to IEC 61249-2-21 Available
- TrenchFET® Power MOSFET
- New Low Thermal Resistance PowerPAK® Package, ¹/₃ the Space of An SO-8 While Thermally Comparable



COMPLIANT HALOGEN **FREE**

APPLICATIONS

- Synchronous Rectification
- Primary Side Switch





N-Channel MOSFET

3.30 mm 3.30 mm **Bottom View**

PowerPAK 1212-8

Ordering Information: Si7220DN-T1-E3 (Lead (Pb)-free)

Si7220DN-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS Parameter	Symbol	10 s	Steady State	Unit	
Drain-Source Voltage		V _{DS}	60		V
Gate-Source Voltage		V_{GS}	± 20		
Out 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1	T _A = 25 °C	- I _D	4.8	3.4	^
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 70 °C		3.8	2.7	
Pulsed Drain Current		I _{DM}	20		Α
Avalanche Current	L = 0.1 mH	I _{AS}	11 6.1		
Single Avalanche Energy	L=UIIIIII	E _{AS}			mJ
Continuous Source Current (Diode Conduction) ^a		I _S	2.2	1.1	Α
N . D D	T _A = 25 °C	- P _D	2.6	1.3	W
Maximum Power Dissipation ^a	T _A = 70 °C		1.4	0.69	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		°C
Soldering Recommendations (Peak Temperature) ^{b, c}			260		

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Marrian de Ambienta	t ≤ 10 s	R _{thJA}	38	48	°C/W	
Maximum Junction-to-Ambient ^a	Steady State		77	94		
Maximum Junction-to-Case (Drain)	Steady State	R_{thJC}	4.3	5.4		

- a. Surface Mounted on 1" x 1" FR4 board.
- b. See Solder Profile (www.vishay.com/ppg273257). The PowerPAK 1212-8 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- c. Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.

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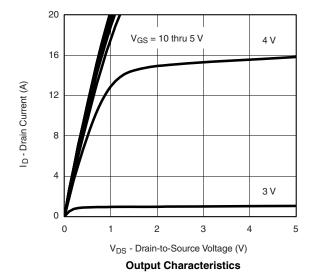
Parameter	Symbol	Test Conditions Min.		Тур.	Max.	Unit	
Static				•			
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$			3	V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 60 V, V _{GS} = 0 V		1			
		$V_{DS} = 60 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 85 ^{\circ}\text{C}$			5	μΑ	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	20			Α	
Drain-Source On-State Resistance ^a	В	$V_{GS} = 10 \text{ V}, I_D = 4.8 \text{ A}$		0.048	0.060	0.060 0.075	
	R _{DS(on)} –	$V_{GS} = 4.5 \text{ V}, I_D = 4.3 \text{ A}$		0.061	0.075		
Forward Transconductance ^a	9 _{fs}	$V_{DS} = 10 \text{ V}, I_D = 4.8 \text{ A}$		15		S	
Diode Forward Voltage ^a	V _{SD}	$I_S = 2.2 \text{ A}, V_{GS} = 0 \text{ V}$		0.8	1.2	V	
Dynamic ^b				•			
Total Gate Charge	Q_g			13	20	nC	
Gate-Source Charge	Q_{gs}	$V_{DS} = 30 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 4.8 \text{ A}$		2.3			
Gate-Drain Charge	Q _{gd}			2.6			
Gate Resistance	R_{g}	f = 1 MHz		2		Ω	
Turn-On Delay Time	t _{d(on)}			10	15		
Rise Time	t _r	V_{DD} = 30 V, R_L = 30 Ω		10	15		
Turn-Off Delay Time	t _{d(off)}	$t_{d(off)}$ $I_D \cong 1 \text{ A, } V_{GEN} = 10 \text{ V, } R_g = 6 \Omega$		20	30	ns	
Fall Time	t _f			10	15		
Source-Drain Reverse Recovery Time	t _{rr}	I _F = 2.2 A, dI/dt = 100 A/μs		30	60		

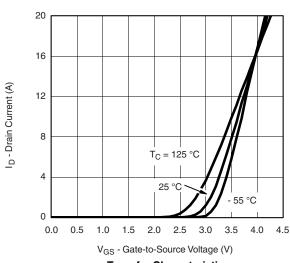
Notes:

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



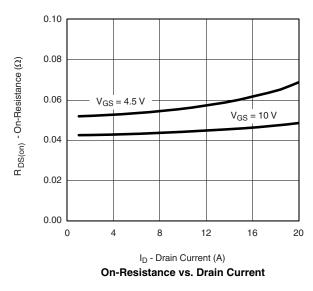


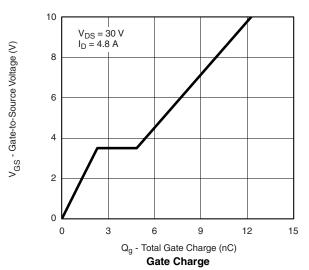


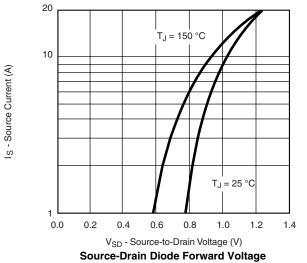




TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



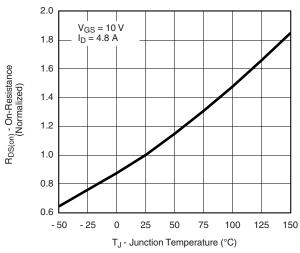




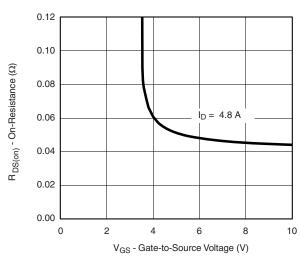
1000 800 C - Capacitance (pF) C_{iss} 600 400 200 Coss 0 40 0 10 20 30 50 60

V_{DS} - Drain-to-Source Voltage (V)

Capacitance



On-Resistance vs. Junction Temperature

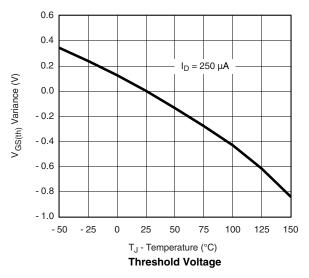


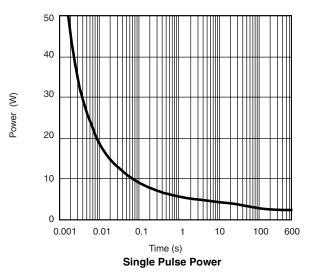
On-Resistance vs. Gate-to-Source Voltage

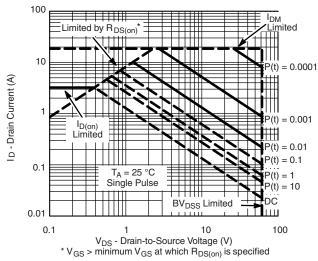
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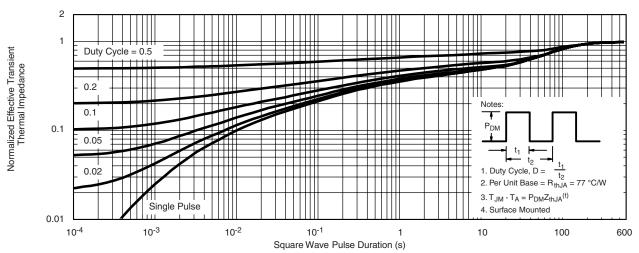
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted







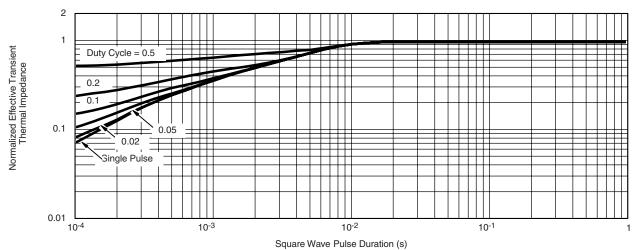
Safe Operating Area, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Ambient



TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Case

Notes:

The minimum creepage between D1 and D2 for this 100 V device is 0.2 mm. Please see PowerPAK 1212-8 outline drawing, document # 71656, for more information.

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